

Amendment to the Specification:

Please replace the Title with the following amended Title:

~~Self Aligned Process Using Indium Gallium Arsenide Etching to Form Reentry Feature in Heterojunction Bipolar Transistor with an Emitter Cap Having a Sidewall with a Reentry Feature Having an Undercut Profile~~

Please replace paragraph [0011] with the following amended paragraph:

[0011] In one embodiment of the invention, a method for forming a heterojunction bipolar transistor (HBT) includes forming an etch mask atop an emitter cap layer of the HBT to expose a portion of the emitter cap layer, and selectively etching the exposed portion of the emitter cap layer to (1) form a reentry feature and (2) to expose a portion of the emitter layer. The method further includes selectively etching the exposed portion of the emitter layer to expose a portion of the base layer, and forming a metal layer over the exposed portion of the base layer and the exposed portion of the emitter cap layer. The heterojunction bipolar transistor has (1) a sub-collector, (2) a collector atop the sub-collector, (3) a base atop the collector, (4) a base contact atop the base, (5) an emitter atop the base, (6) an emitter cap atop the emitter where the emitter cap has a sidewall with a reentry feature having an undercut profile, and (7) an emitter metal atop the emitter cap.